	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	546	(("438/760") or ("438/750"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 13:58			0
2	BRS	L15	473	1 and ((silicon adj1 nitride) or (silicon adj1 oxide) or trench$ or thickness or thick)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 14:03			0
3	BRS	L22	640859	FET or transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 14:04			0
4	BRS	L29	204	22 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 14:02			0
5	BRS	L43	71	15 and LPCVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 14:04			0
6	BRS	L50	65	43 and (gate or dielectric or insulating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 14:04			0
7	BRS	L63	56	50 and (heat$5 or thermal or anneal$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 14:07			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	546	(("438/760") or ("438/750"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 13:58			0
2	BRS	L15	473	1 and ((silicon adj1 nitride) or (silicon adj1 oxide) or trench$ or thickness or thick)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 14:03			0
3	BRS	L43	71	15 and LPCVD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 14:04			0
4	BRS	L50	65	43 and (gate or dielectric or insulating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 14:04			0
5	BRS	L63	56	50 and (heat$5 or thermal or anneal$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 14:12			0
6	BRS	L76	16	63 and trench$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 14:12			0